# DISCRETE SEMICONDUCTORS

# DATA SHEET

# **BUJ105AB**Silicon Diffused Power Transistor

**Product specification** 

October 2001



# **Silicon Diffused Power Transistor**

BUJ105AB

#### **GENERAL DESCRIPTION**

High-voltage, high-speed planar-passivated npn power switching transistor in SOT404 (D²-PAK) surface-mount package intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

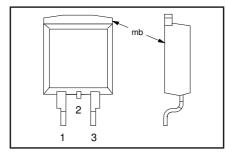
#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V <sub>CESM</sub>	Collector-emitter voltage peak value	$V_{BE} = 0 \text{ V}$	-	700	V
V <sub>CBO</sub>	Collector-Base voltage (open emitter)		-	700	V
V <sub>CEO</sub>	Collector-emitter voltage (open base)		-	400	V
I <sub>C</sub>	Collector current (DC)		-	8	Α
1 1	Collector current peak value		-	16	Α
P <sub>tot</sub>	Total power dissipation	$T_{mb} \le 25 \degree C$	-	125	W
V <sub>CEsat</sub>	Collector-emitter saturation voltage	$I_{\rm C} = 4.0 \text{ A}; I_{\rm B} = 0.8 \text{ A}$	0.3	1.0	V
h <sub>FEsat</sub>		$I_{\rm C} = 4.0 \text{ A}; V_{\rm CE} = 5 \text{ V}$	11	15	
t <sub>f</sub>	Fall time	$I_{\rm C} = 5  \rm A;  I_{\rm B1} = 1  \rm A$	20	50	ns

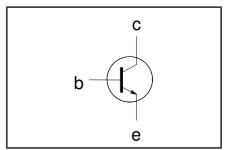
#### **PINNING - SOT404**

PIN	DESCRIPTION	
1	oase	
2	collector	
3	emitter	
mb	collector	

#### **PIN CONFIGURATION**



#### **SYMBOL**



#### **LIMITING VALUES8**

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CESM</sub>	Collector to emitter voltage	$V_{BE} = 0 V$	-	700	V
V <sub>CEO</sub>	Collector to emitter voltage (open base)		-	400	V
V <sub>CBO</sub>	Collector to base voltage (open emitter)		-	700	V
I <sub>C</sub>	Collector current (DC)		-	8	A
I <sub>CM</sub>	Collector current peak value		-	16	Α
I <sub>B</sub>	Base current (DC)		-	4	Α
l 1 <sup>=</sup>	Base current peak value		-	8	Α
P <sub>tot</sub>	Total power dissipation	T <sub>mb</sub> ≤ 25 °C	-	125	W
T <sub>stq</sub>	Storage temperature		-65	150	°C
T <sub>i</sub>	Junction temperature		-	150	°C

#### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{thj-mb}$	Thermal resistance junction to mounting base		1	1.0	K/W
R <sub>th i-a</sub>	Thermal resistance junction to ambient	minimum footprint, FR4 board	55	-	K/W

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# STATIC CHARACTERISTICS

 $T_{mb}$  = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CES</sub> ,I <sub>CBO</sub>	Collector cut-off current <sup>1</sup>		-	-	0.2 0.5	mA mA
$I_{CEO}$ $I_{EBO}$ $V_{CEOsust}$	Collector cut-off current Emitter cut-off current Collector-emitter sustaining voltage	$egin{array}{l} V_{\text{CEO}} = V_{\text{CEOMmax}}  (400 \text{V}) \ V_{\text{EB}} = 9  \text{V};  I_{\text{C}} = 0  \text{A} \ I_{\text{B}} = 0  \text{A};  I_{\text{C}} = 10  \text{mA}; \ L = 25  \text{mH} \end{array}$	- - 400	- - -	0.1 1 -	mA mA V
$egin{array}{l} V_{\text{CEsat}} \ V_{\text{BEsat}} \ h_{\text{FE}} \ h_{\text{FE}} \ h_{\text{FEsat}} \end{array}$	Collector-emitter saturation voltage Base-emitter saturation voltage DC current gain	$ \begin{aligned} &I_{C} = 4.0 \text{ A;} I_{B} = 0.8 \text{ A} \\ &I_{C} = 4.0 \text{ A;} I_{B} = 0.8 \text{ A} \\ &I_{C} = 1 \text{ mA;} \text{ V}_{CE} = 5 \text{ V} \\ &I_{C} = 500 \text{ mA;} \text{ V}_{CE} = 5 \text{ V} \\ &I_{C} = 4.0 \text{ A;} \text{ V}_{CE} = 5 \text{ V} \end{aligned} $	- - 10 13 8	0.3 1.0 14 23 11	1.0 1.5 34 36 15	V

#### **DYNAMIC CHARACTERISTICS**

 $T_{mb}$  = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (resistive load)	$I_{Con} = 5 \text{ A}; I_{Bon} = -I_{Boff} = 1 \text{ A}; R_L = 75 \text{ ohms}; V_{BB2} = 4 \text{ V};$			
$t_{on}$ $t_{s}$ $t_{f}$	Turn-on time Turn-off storage time Turn-off fall time		0.65 1.8 0.3	1 2.5 0.5	μs μs μs
	Switching times (inductive load)	$I_{Con} = 5 \text{ A}; I_{Bon} = 1 \text{ A}; L_{B} = 1 \mu\text{H}; -V_{BB} = 5 \text{ V}$			
t <sub>s</sub> t <sub>f</sub>	Turn-off storage time Turn-off fall time	· BB	1.2 20	1.7 50	μs ns
	Switching times (inductive load)	$I_{Con} = 5 \text{ A}; I_{Bon} = 1 \text{ A}; L_{B} = 1 \mu\text{H}; -V_{BB} = 5 \text{ V}; T_{i} = 100 ^{\circ}\text{C}$			
t <sub>s</sub> t <sub>f</sub>	Turn-off storage time Turn-off fall time	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	1.4 25	1.9 100	μs ns

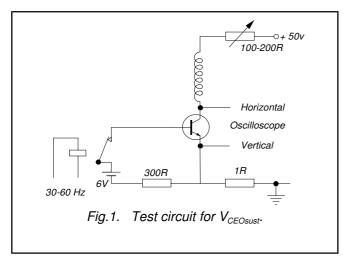
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<sup>1</sup> Measured with half sine-wave voltage (curve tracer).

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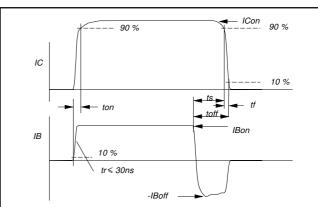
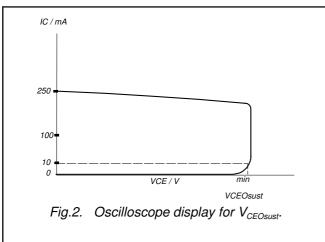
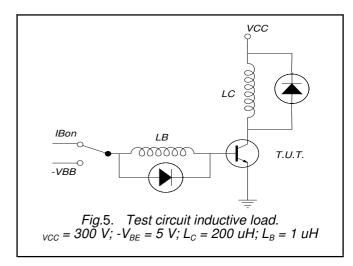
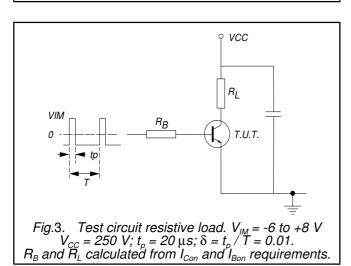
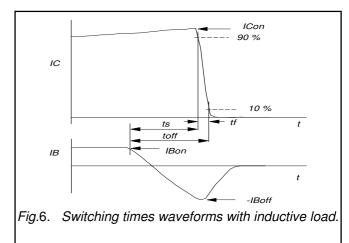


Fig.4. Switching times waveforms with resistive load.



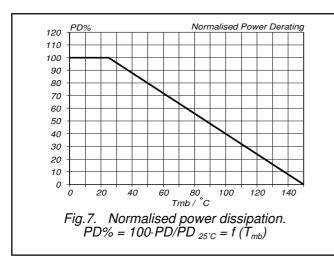


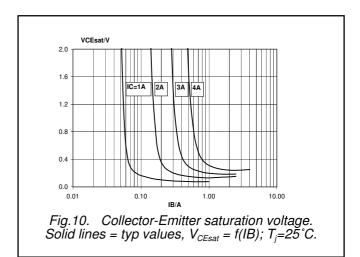


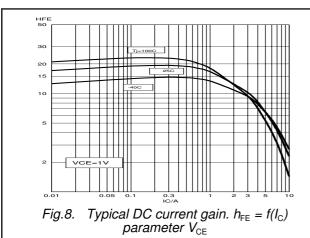


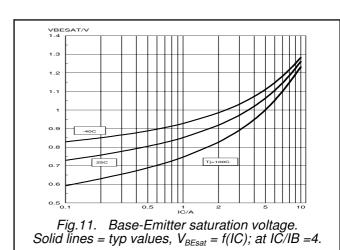
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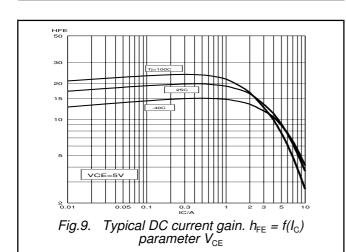
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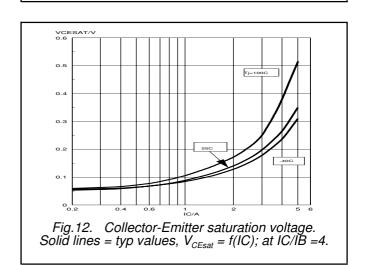








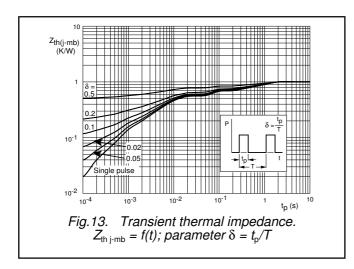




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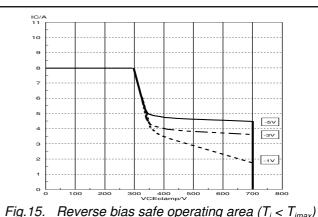


Fig.15. Reverse bias safe operating area  $(T_j < T_{jmax})$  for  $-V_{BE} = 5V, 3V \& 1V$ .

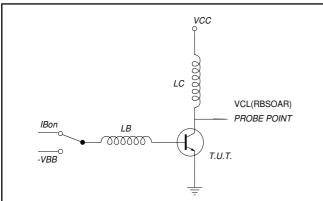


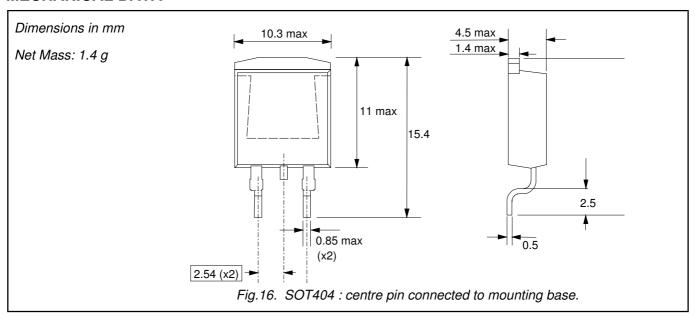
Fig.14. Test circuit for reverse bias safe operating area.

$$\begin{split} V_{clamp} < 700V; \ V_{cc} = 150V; \ -V_{be} = 5V, 3V \ \& \ 1V; \\ L_B = 1 \mu H; \ L_C = 200 \mu H. \end{split}$$

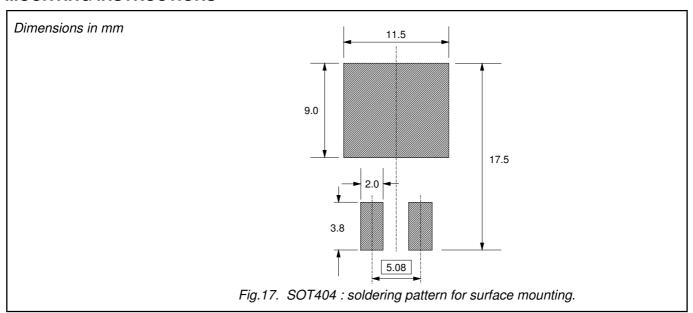
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## **MECHANICAL DATA**



#### **MOUNTING INSTRUCTIONS**



#### **Notes**

1. Plastic meets UL94 V0 at 1/8".

### Legal information

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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